


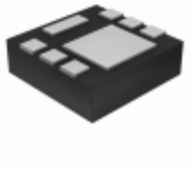





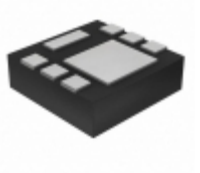
	<h2>RF4E080BNTTR</h2>
	<p><b>Hersteller-Teilenummer:</b> RF4E080BNTTR</p> <p><b>Hersteller / Marke:</b> LAPIS Semiconductor</p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 8A 8-HUML</p> <p><b>Datenblätter:</b>  <a href="#">RF4E080BNTTR.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 12000 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	RF4E080BNTTR
Hersteller	LAPIS Semiconductor
Beschreibung	MOSFET N-CH 30V 8A 8-HUML
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	12000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	150 °C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-PowerUDFN
Supplier Device-Gehäuse	6-HUML2020L8 (2x2)
Verlustleistung (max)	2W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8A (Ta)
Rds On (Max) @ Id, Vgs	17.6 mOhm @ 8A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	14.5nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	660pF @ 15V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)



















































RF4E080BNTTR ist neu im Original, Suche RF4E080BNTTR Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie RF4E080BNTTR LAPIS Semiconductor mit Garantie und Vertrauen. Anfrage RF4E080BNTTR: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>RF4E080GNTR</b> LAPIS Semiconductor MOSFET N-CH 30V 8A 8-HUML</p>	 <p><b>RF4E075AT</b> ROHM ROHM QFN</p>	 <p><b>RF4E080BN TB</b> ROHM RF4E080BN TB ROHM</p>	 <p><b>RF4E100AJTCR</b> LAPIS Semiconductor NCH 30V 10A MIDDLE POWER MOSFET</p>
 <p><b>RF4E110GN</b> ROHM ROHM QFN</p>	 <p><b>RF4E075AT TCR</b> ROHM RF4E075AT TCR ROHM</p>	 <p><b>RF4E080BN</b> ROHM RF4E080BN ROHM</p>	 <p><b>RF4E110BNTTR</b> LAPIS Semiconductor MOSFET N-CH 30V 11A 8-HUML</p>

### heiße Teile

Mehr

 1210R-102J	 1M500S-050-01	 2N6027RL1G	 A70QS200-4	 B2405S-3W
 CDNBS16-T12	 DD171N16KOF	 DDTC115EUA-7	 DF10-48S05	 DMN5L06K-7
 FDS6572A	 GRM0225C1E1R9CA03L	 GRM2196P2A4R9CD01D	 MWA20-24S15	 P140CH02CM0
 PS2505L-2	 PT5110E23C-15	 R5F212A7SN-A78FP	 RF4013GFE8	 RF4013TRN7
 RF4016-000	 RF4018-000	 RF4021-000	 RF4165-000	 RF4180ATR13
 RF4180DTR13	 RF4180TR13	 RF430CL330HCPWR	 RF430F5144BIRKVRQ1	 RF430F5144CIRKVRQ1
 RF430F5144Q1	 RF430F5144S1	 RF430F5144SQ1-1	 RF430F5155AQ1-1	 RF430F5175AQ1-1
 RF430F5175T1	 RF430V5140AQ1	 RF4C050AP	 RF4E075ATTCTR	 RF4E080BN
 RF4E080GNTR	 RF4E110BN	 RMC1-151JTE	 S-8211CAK-I6T1U	 SMAJ160A-13-F
 SMPI0905HW-R82M-K01	 SQR40N10-25-GE3	 T1270N36TOF	 TL431ASA-7	 VN02NPT13TR

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